

BTB04

TRIAC

SENSITIVE GATE TRIACS

■ DESCRIPTION

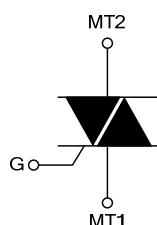
The UTC **BTB04** is a 4A triacs, it uses UTC's advanced technology to provide customers with high commutation performances.

The UTC **BTB04** is suitable for inductive loads, general purpose AC switching and an ON/OFF function in applications such as induction motor starting circuits, for phase control operation in light dimmers and static relays, etc.

■ FEATURES

- * Low gate trigger current
- * Low holding current

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
BTB04L-x-x-T60-K	BTB04G-x-x-T60-K	TO-126	MT1	MT2	G	Bulk
BTB04L-x-x-TA3-T	BTB04G-x-x-TA3-T	TO-220	MT1	MT2	G	Tube
BTB04L-x-x-TM3-T	BTB04G-x-x-TM3-T	TO-251	MT1	MT2	G	Tube
BTB04L-x-x-TN3-R	BTB04G-x-x-TN3-R	TO-252	MT1	MT2	G	Tape Reel
BTB04L-x-x-TND-T	BTB04G-x-x-TND-T	TO-252D	MT1	MT2	G	Tube

Note: Pin Assignment: MT1: MT1 MT2: MT2 G: Gate

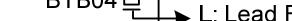
	(1)K: Bulk, T: Tube, R: Tape Reel
	(2)T60: TO-126, TA3: TO-220, TM3: TO-251
	TN3: TO-252, TND: TO-252D
	(3)refer to SENSITIVITY AND TYPE
	(4)4: 400V, 6: 600V, 8: 800V
(5)G: Halogen Free and Lead Free, L: Lead Free	

■ SENSITIVITY AND TYPE

PART NUMBER	VOLTAGE			SENSITIVITY	TYPE
	400V	600V	800		
A	◎	◎		10mA	STANDARD
S		◎		10mA	STANDARD
D	◎			5mA	STANDARD
T	◎	◎	◎	5mA	STANDARD

◎: Available

■ MARKING

TO-126	TO-220 / TO-251 / TO-252 / TO-252D
 <p>1</p> <p>UTC <input type="checkbox"/> <input type="checkbox"/> <input type="checkbox"/> <input type="checkbox"/> BTB04 <input type="checkbox"/></p> <p>Date Code</p> <p>L: Lead Free G: Halogen Free</p>	 <p>1</p> <p>UTC BTB04 <input type="checkbox"/></p> <p>Lot Code</p> <p>L: Lead Free G: Halogen Free Date Code</p>

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
RMS On-State Current (360° Conduction Angle)	$T_C=90^\circ\text{C}$	$I_{T(\text{RMS})}$	4	A
Non Repetitive Surge Peak On-State Current (T_J initial=25°C)	$t_p=8.3\text{ms}$	I_{TSM}	42	A
	$t_p=10\text{ms}$		40	A
I^2t Value	$t_p=10\text{ms}$	I^2t	8	A^2s
Critical Rate of Rise of On-State Current: $I_G=50\text{mA}$, $dI_G/dt=0.1\text{A}/\mu\text{s}$	Repetitive $F=50\text{Hz}$	dI/dt	10	$\text{A}/\mu\text{s}$
	Non Repetitive		50	$\text{A}/\mu\text{s}$
Repetitive Peak Off-State Voltage ($T_J=110^\circ\text{C}$)	400 T/D	V_{DRM}/V_{RRM}	400	V
	600 T/S		600	V
	800 T		800	V
Peak Gate Current	$t_p=20\mu\text{s}$	I_{GM}	4	A
Peak Positive Gate Voltage	$t_p=20\mu\text{s}$	V_{GM}	16	V
Peak Positive Gate Power Dissipation	$t_p=20\mu\text{s}$	P_{GM}	40	W
Average Gate Power Dissipation		$P_{G(AV)}$	1	W
Operating Junction Temperature		T_J	-40 ~ +110	°C
Storage Junction Temperature		T_{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-126	θ_{JA}	100	°C/W
	TO-220		60	°C/W
	TO-251/TO-252		100	°C/W
	TO-252D			
Junction to Case (AC)	TO-126	θ_{JC}	3.7	°C/W
	TO-220		2.4	°C/W
	TO-251/TO-252		2.6	°C/W
	TO-252D			

■ ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS	T			D			S			A			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
Gate Trigger Current	I_{GT}	$V_D=12V$ (DC) $R_L=33\Omega$ $T_J=25^\circ C$	I-II-III		5			5			10			10	mA
			IV		5			10			10			25	mA
Gate Trigger Voltage	V_{GT}	$T_J=25^\circ C$	ALL		1.5			1.5			1.5			1.5	V
Gate Non-Trigger Voltage	V_{GD}	$V_D=V_{DRM}$, $R_L=3.3k\Omega$, $T_J=110^\circ C$	ALL	0.2		0.2			0.2		0.2				V
Time Gate Trigger	t_{GT}	$V_D=V_{DRM}$, $I_G=40mA$, $dI_G/dt=0.5A/\mu s$, $T_J=25^\circ C$	ALL		2			2			2		2		μs
Holding Current (Note 1)	I_H	$I_T=100mA$, Gate Open, $T_J=25^\circ C$			15			15			25			25	mA
Latching Current	I_L	$I_G=1.2I_{GT}$, $T_J=25^\circ C$	I-III-IV	10		10			20			20			mA
Peak On-State Voltage (Note 1)	V_{TM}	$I_{TM}=5.5A$, $t_p=380\mu s$, $T_J=25^\circ C$			1.65			1.65			1.65			1.65	V
			II	20		20			40			40			mA
Critical Rate of Rise of Off-State Voltage (Note 1)	dV/dt	Linear Slope up to $V_D=67\%V_{DRM}$, Gate Open, $T_J=110^\circ C$		10		10		10			10				$V/\mu s$
Critical Rate of Rise of Off-State Voltage at Commutation (Note 1)	$(dV/dt)c$	$(dI/dt)c=1.8A/ms$, $T_J=110^\circ C$		1		1			5			5			$V/\mu s$

Note: For either polarity of electrode MT2 voltage with reference to electrode MT1.

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